

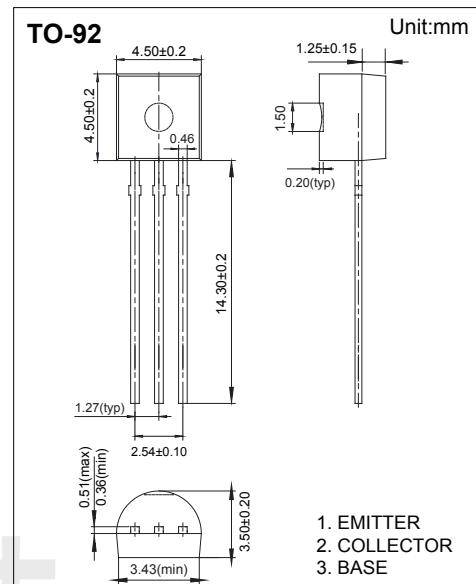
Transistor

NPN Transistors

2SC3279

■ Features

- Low Saturation Voltage
- High DC Current Gain and Excellent hFE Linearity



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	30	V
Collector - Emitter Voltage	V _{C0}	10	
Emitter - Base Voltage	V _{E0}	6	
Collector Current - Continuous	I _c	2	
Collector Power Dissipation	P _c	0.75	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V _{CB0}	I _c = 1 mA, I _e =0	30			V
Collector- emitter breakdown voltage	V _{C0}	I _c = 10 mA, I _b =0	10			
Emitter - base breakdown voltage	V _{E0}	I _e = 1 mA, I _c =0	6			
Collector cut-off current	I _{CB0}	V _{CB} = 30 V, I _e =0			0.1	μA
Emitter cut-off current	I _{E0}	V _{EB} = 6V , I _c =0			0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =2A, I _b = 100mA			0.82	V
Base - emitter saturation voltage	V _{BE(sat)}	I _c =2A, I _b = 100mA			1.2	
Base-emitter voltage	V _{BE}	V _{CE} = 1V, I _c = 2A			1.5	
DC current gain	h _{FE}	V _{CE} = 1V, I _c = 0.5A	140		600	
Collector Output Capacitance	C _{ob}	V _{CB} =10V,I _e =0,f=1MHZ		27		pF
Transition frequency	f _t	V _{CE} = 1V, I _c = 0.5A		150		MHz

■ Classification of hFE

Rank	L	M	N	P
Range	140-240	200-330	300-450	420-600